

# Outline

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- **Background of low-power app's**
- **Concept of SCCMOS**
- **Comparison with other schemes**
- **Measured results**
- **Summary**

# Background of low-voltage applications

- **Strong low-power requirement**

- **Power  $\propto V_{DD}^2$**

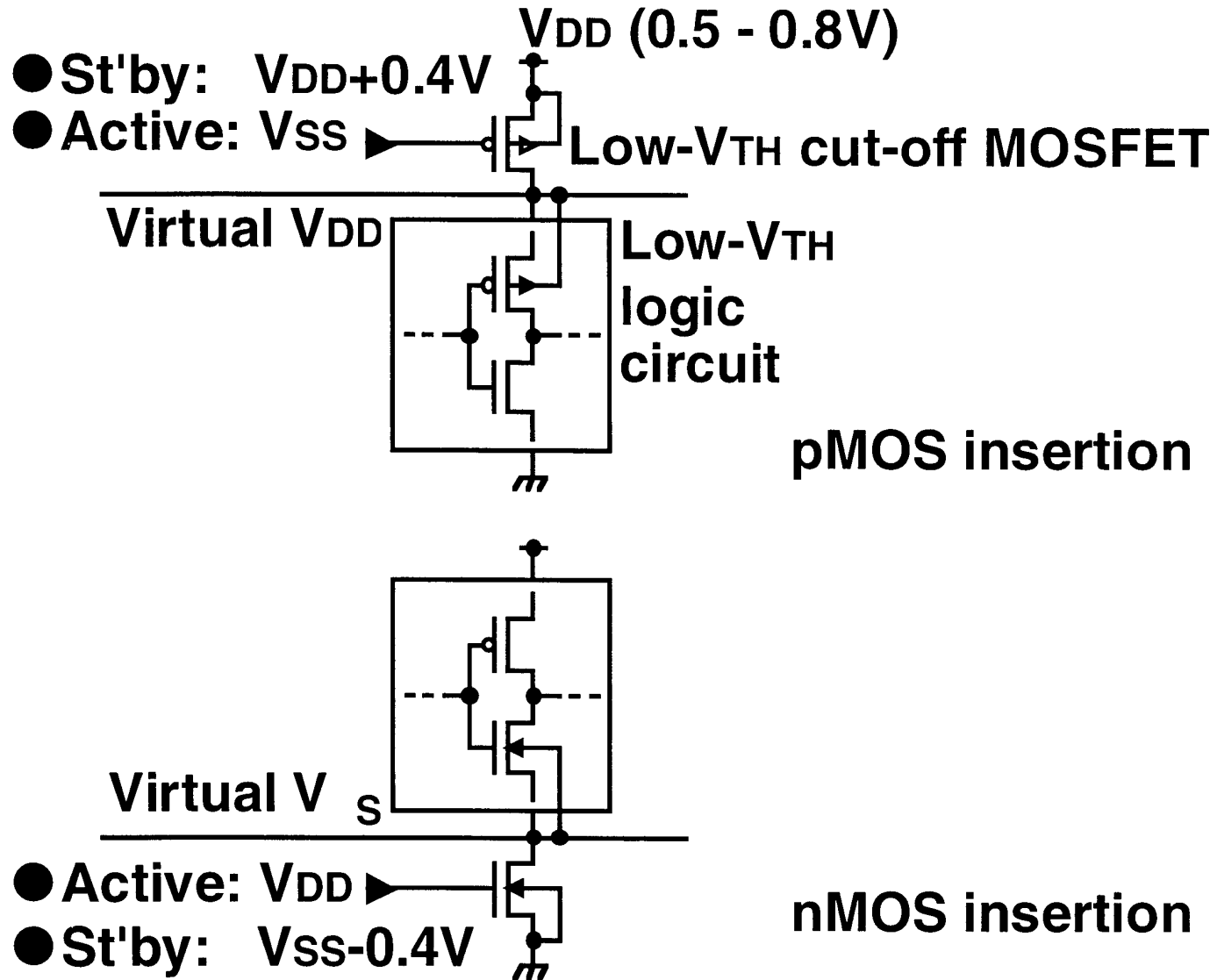
  - **Low  $V_{DD}$  (0.5 - 0.8V)**

  - **Low  $V_{TH}$  (0.1 - 0.2V)**

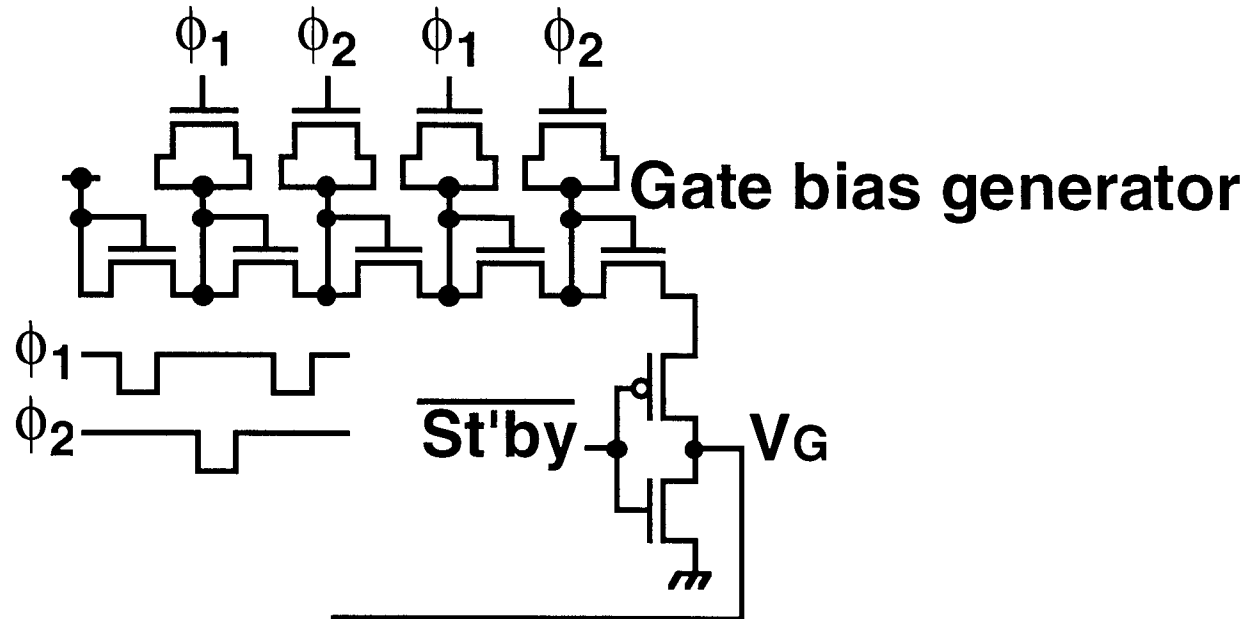
- **10mA-order leakage (1M-gate)**

- **Problem for mobile applications**

# Concept of SCCMOS



# Gate bias generator

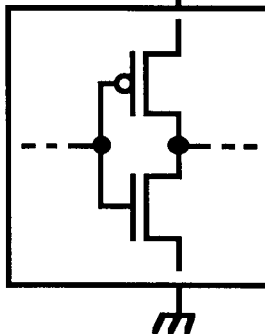


St'by:  $V_{DD}+0.4V$   
Active:  $V_{SS}$

$V_{DD}$  (0.5 - 0.8V)

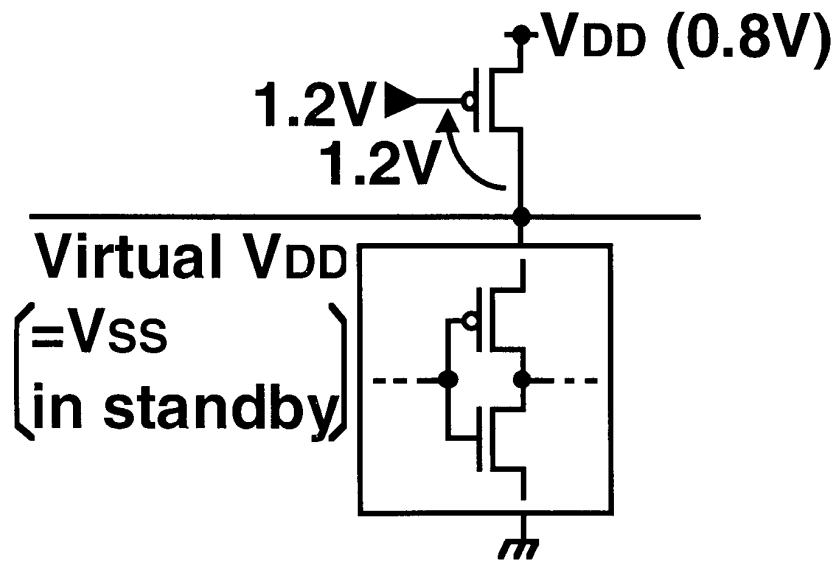
Low- $V_{TH}$  cut-off MOSFET

Virtual  $V_{DD}$

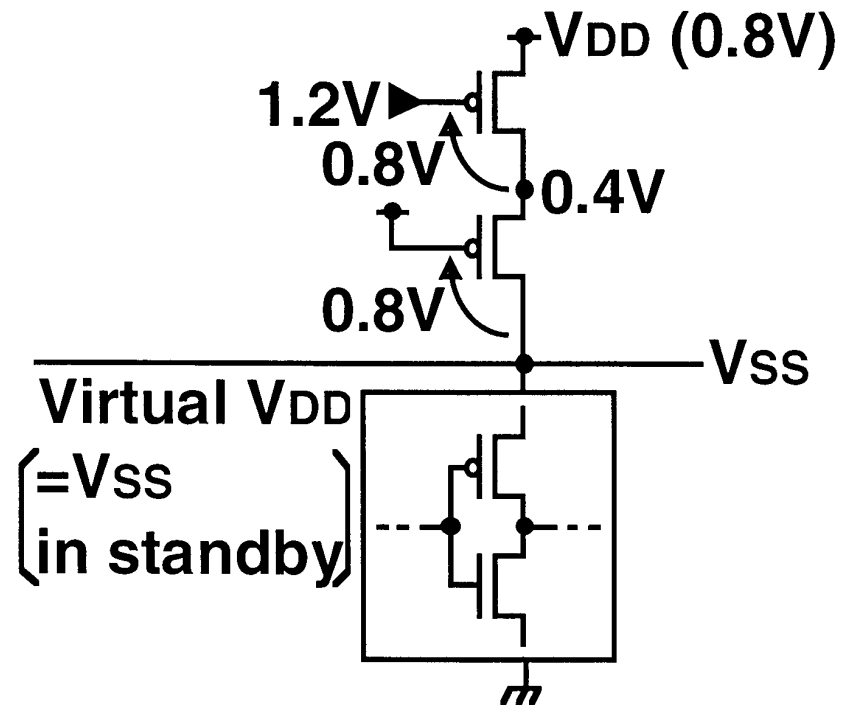


# Oxide reliability

## Original



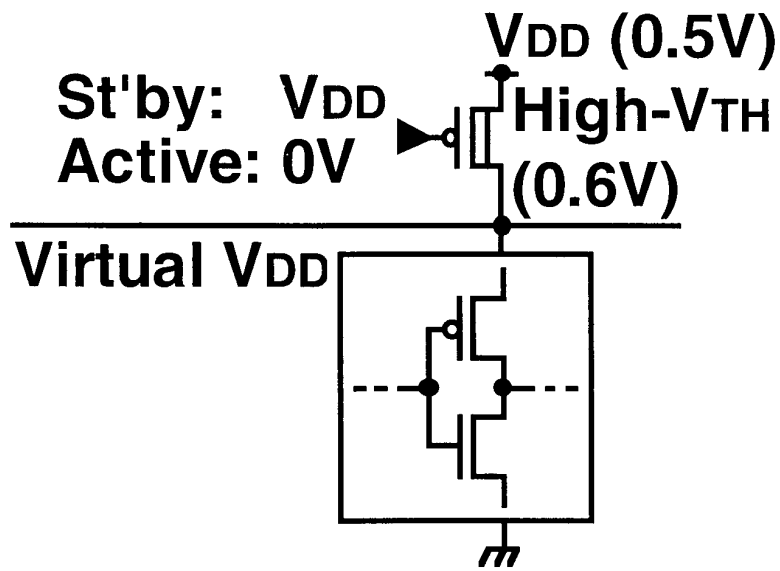
## Higher reliability



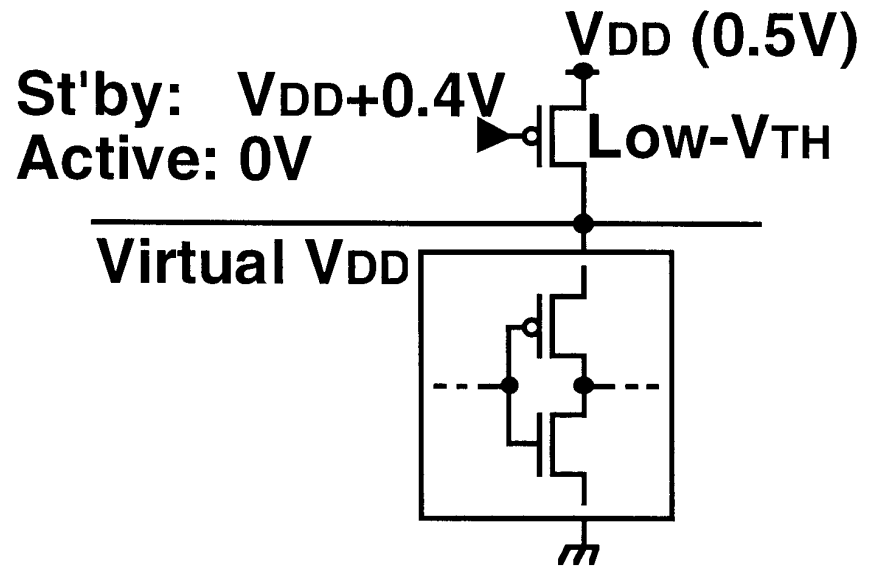
# MTCMOS vs. SCCMOS

- High- $V_{TH}$  MOSFET doesn't turn on at low  $V_{DD}$ .

## MTCMOS



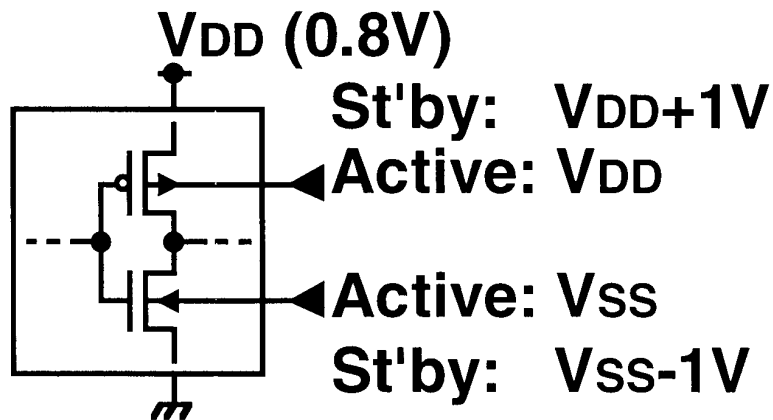
## SCCMOS



# VTCMOS vs. SCCMOS

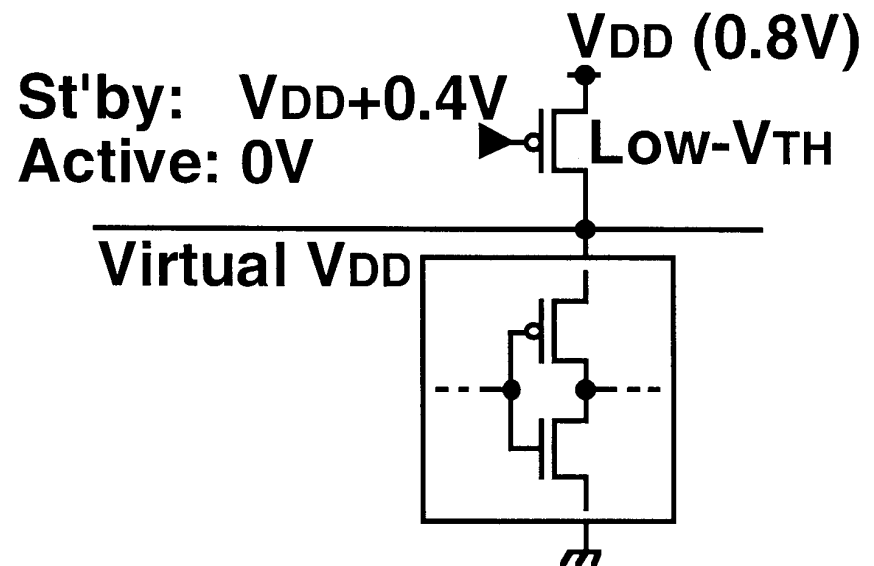
- VTCMOS is not suitable for SOI technology.

## VTCMOS



- $V_{TH}$  varies with body bias effect.

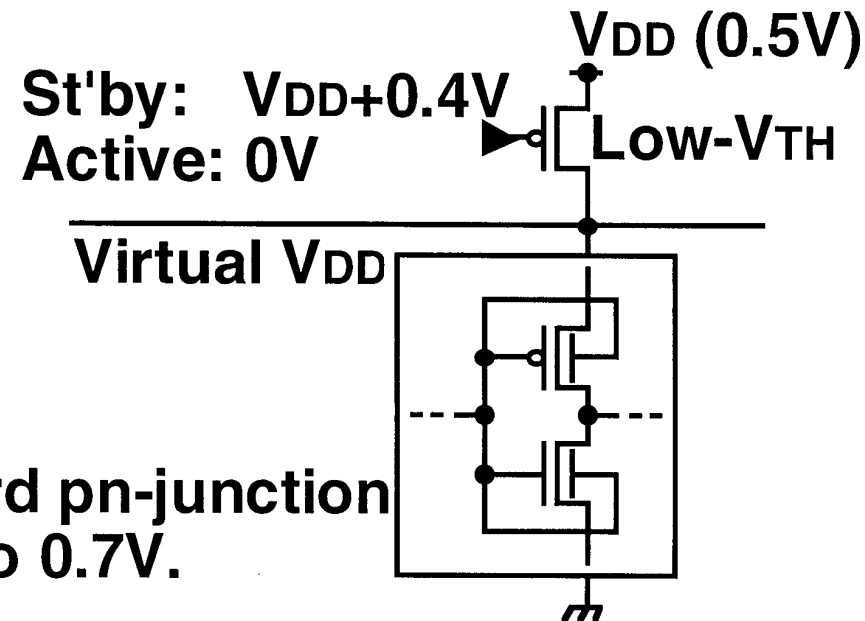
## SCCMOS



# Applicability to DTMOS

- DTMOS suffers 10mA-order leakage (1M-gate).
- SCCMOS can cut off leakage when used with DTMOS.

## DTMOS



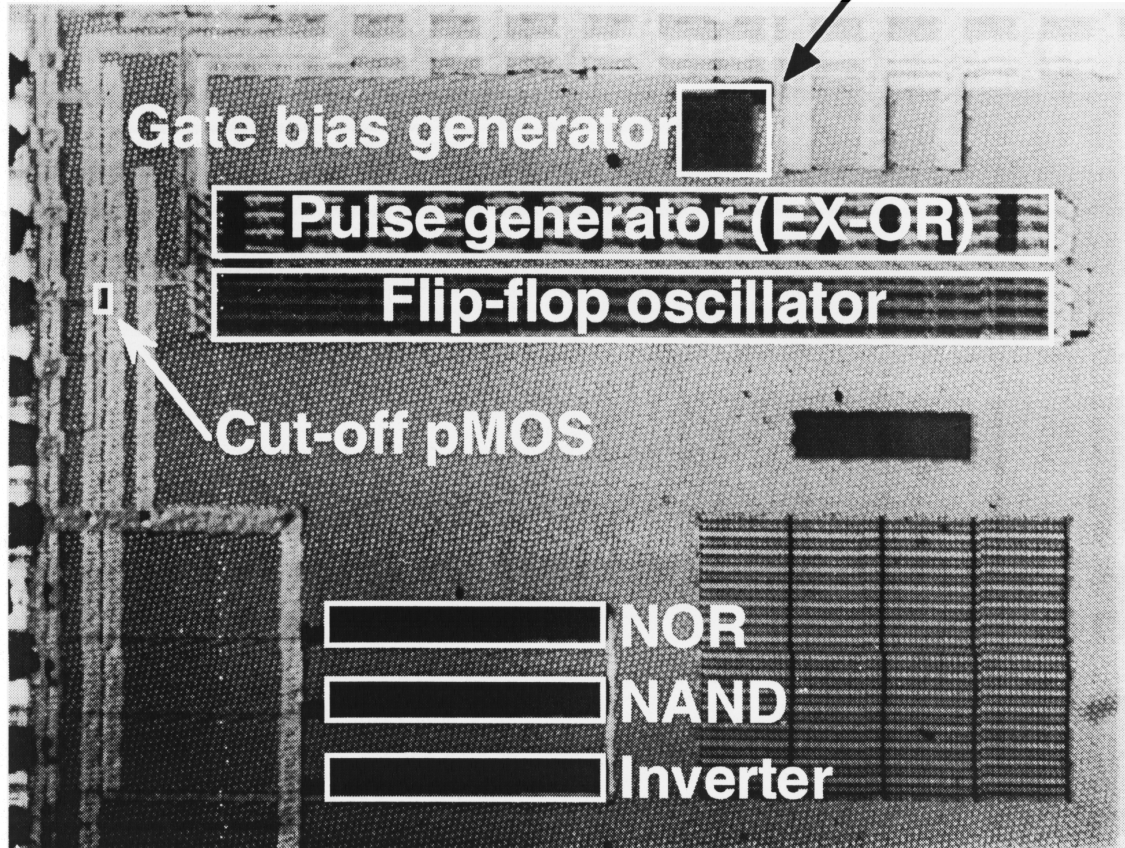
- Inherent forward pn-junction
- $V_{DD}$  is limited to 0.7V.



# Chip microphotograph

- 0.3 $\mu\text{m}$ , triple-metal CMOS process
- $V_{\text{TH}}=0.2\text{V}$

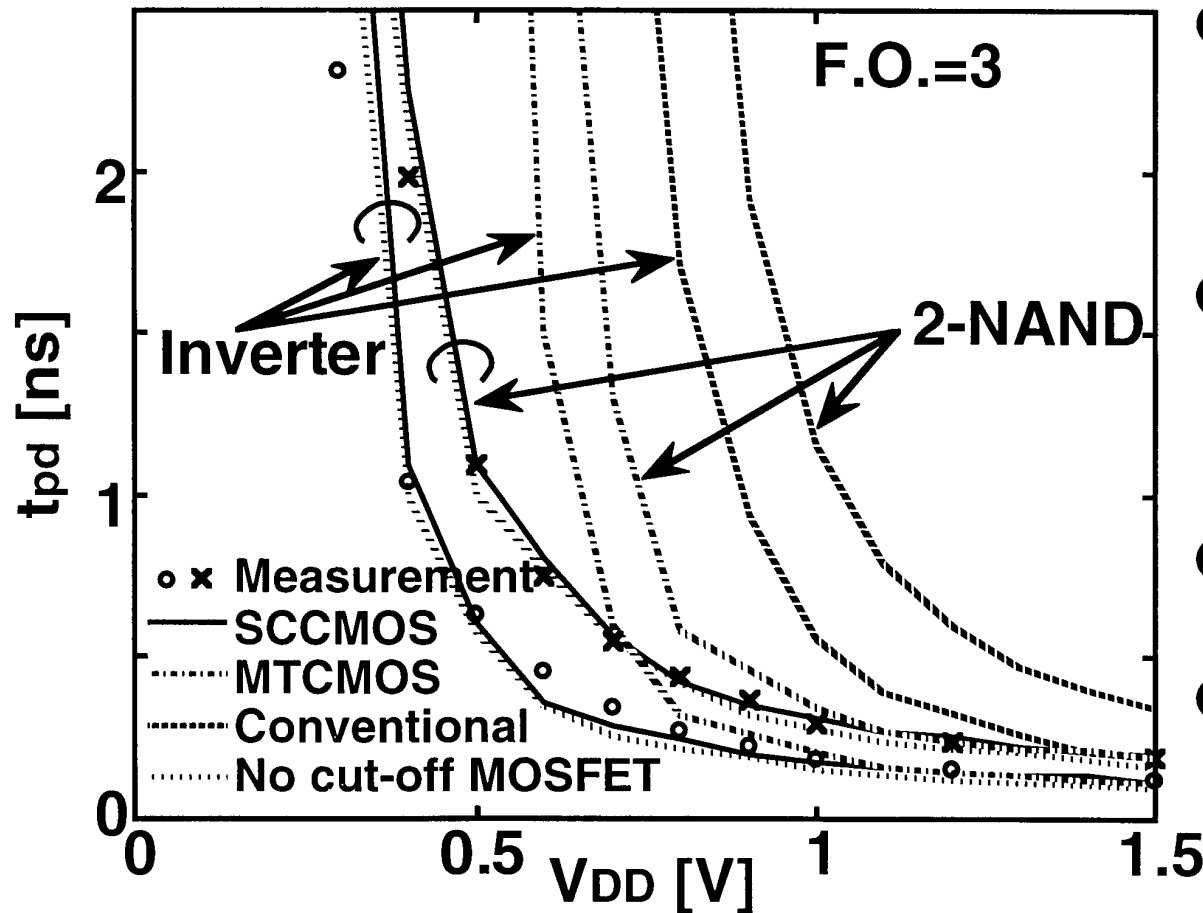
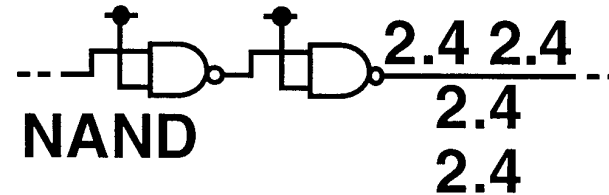
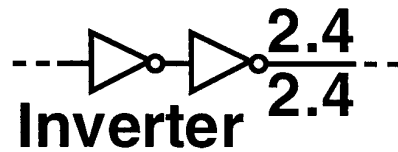
100x100 $\mu\text{m}^2$   
pumping freq=10kHz  
0.1 $\mu\text{A}$  (@  $V_{\text{DD}}=0.5\text{V}$ )



# Delay characteristics (inverter & NAND)

● MOSFET gate widths are  $2.4\mu\text{m}$ .

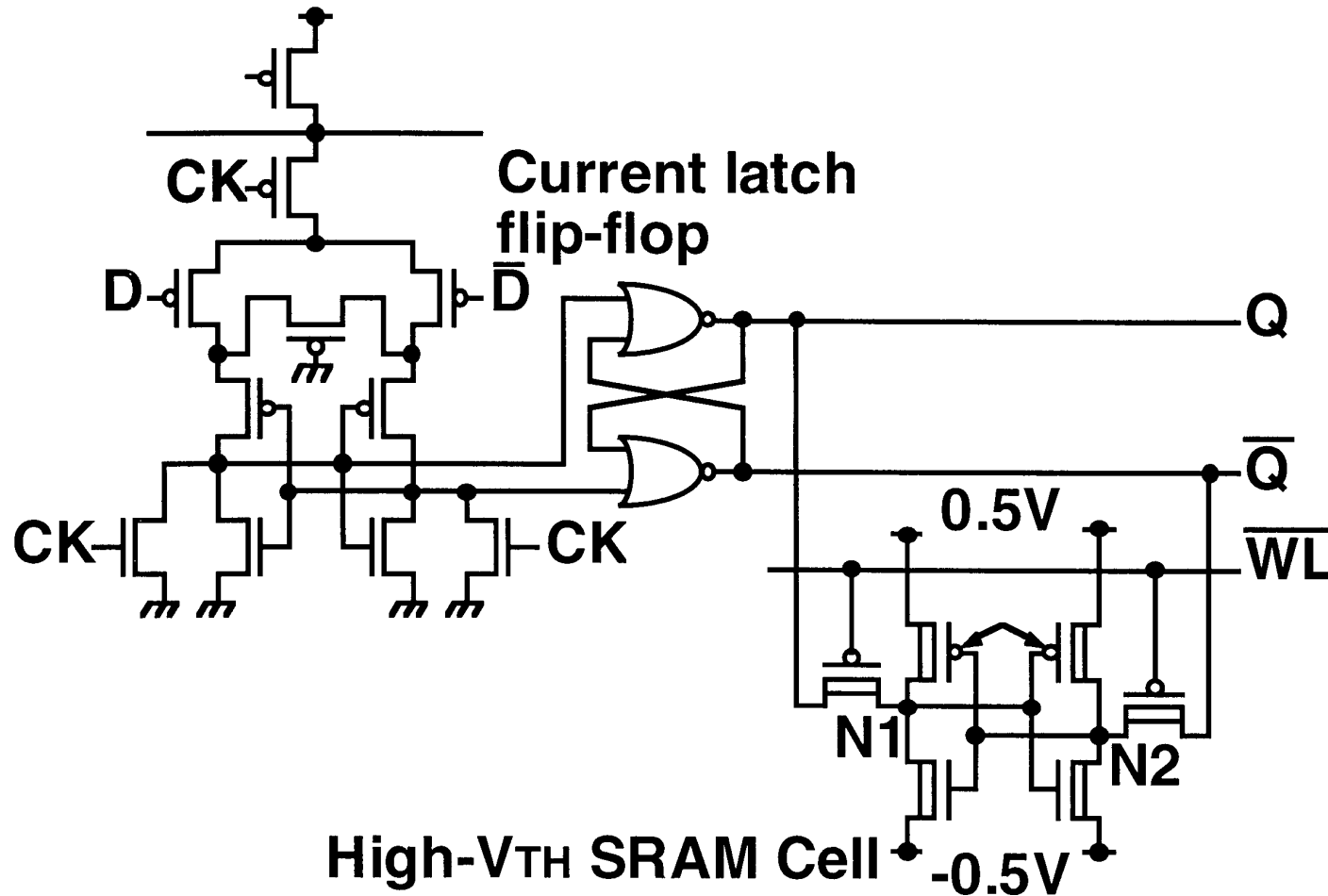
● Fanout-3



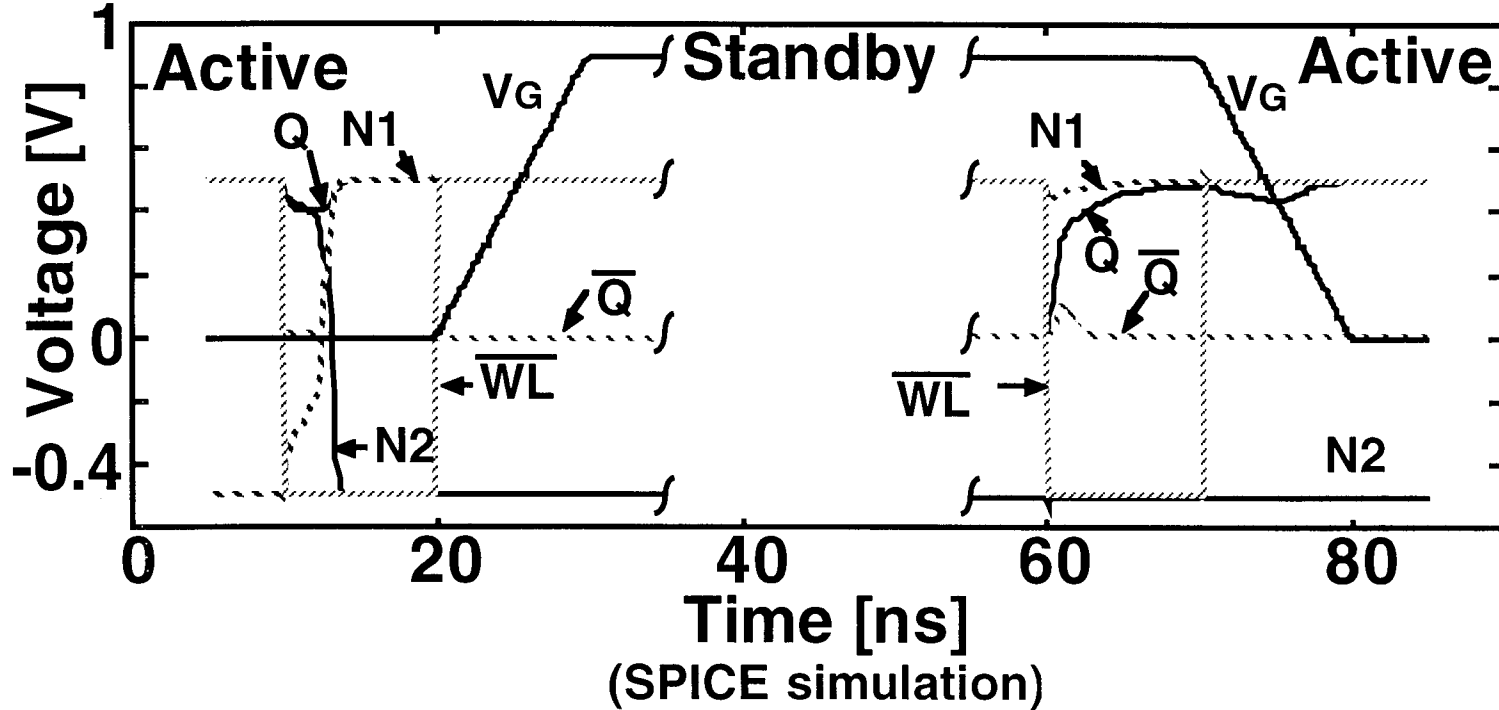
- SCCMOS  
0.2V circuit  
with 0.2V  $V_{TH}$   
cut-off MOSFET
- MTCMOS  
0.2V circuit  
with 0.6V  $V_{TH}$   
cut-off MOSFET
- Conventional  
All 0.6V circuit
- No cut-off MOSFET  
All 0.2V circuit

# Losing information in standby

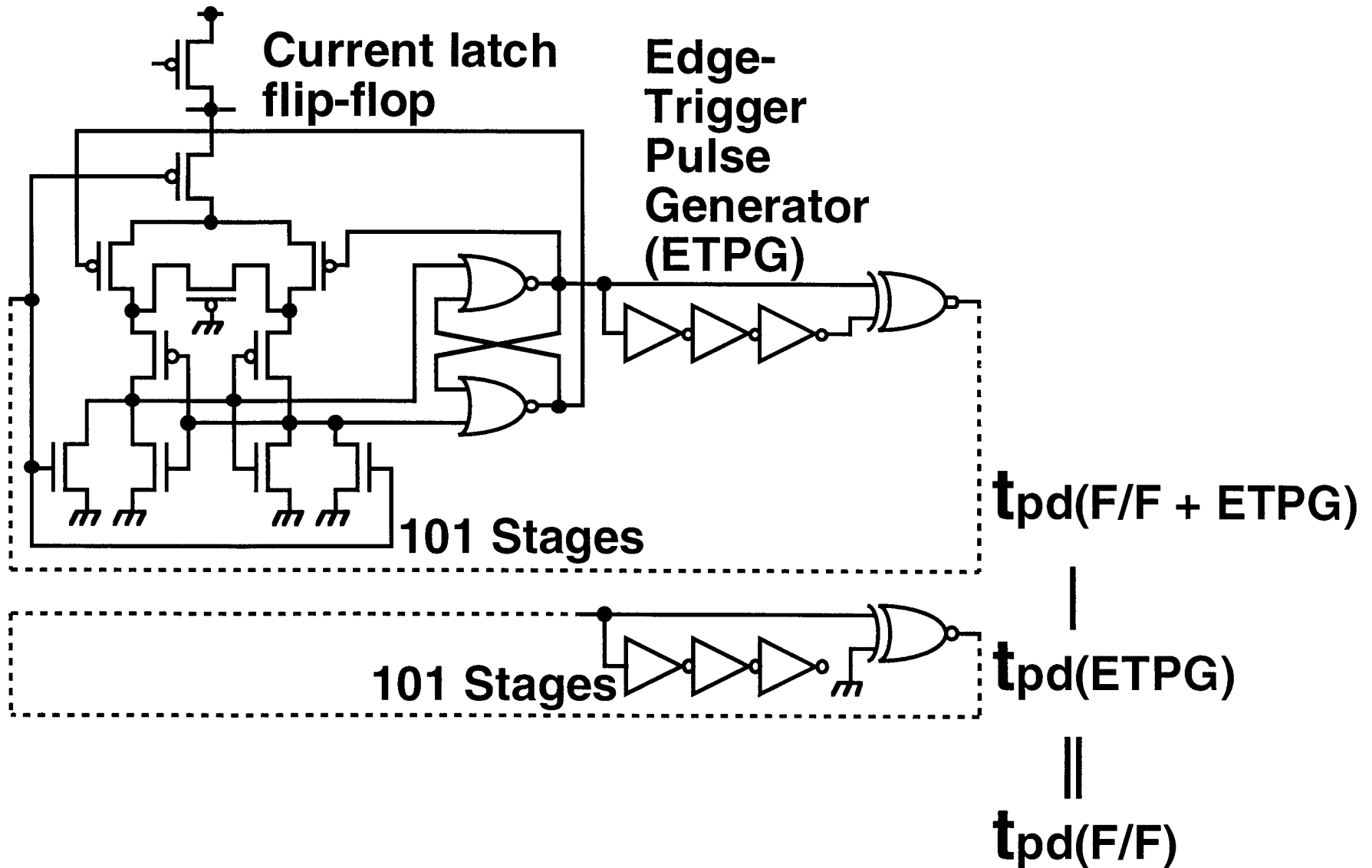
- System level solution: → Using scan-path flip-flops
- Circuit level solution:



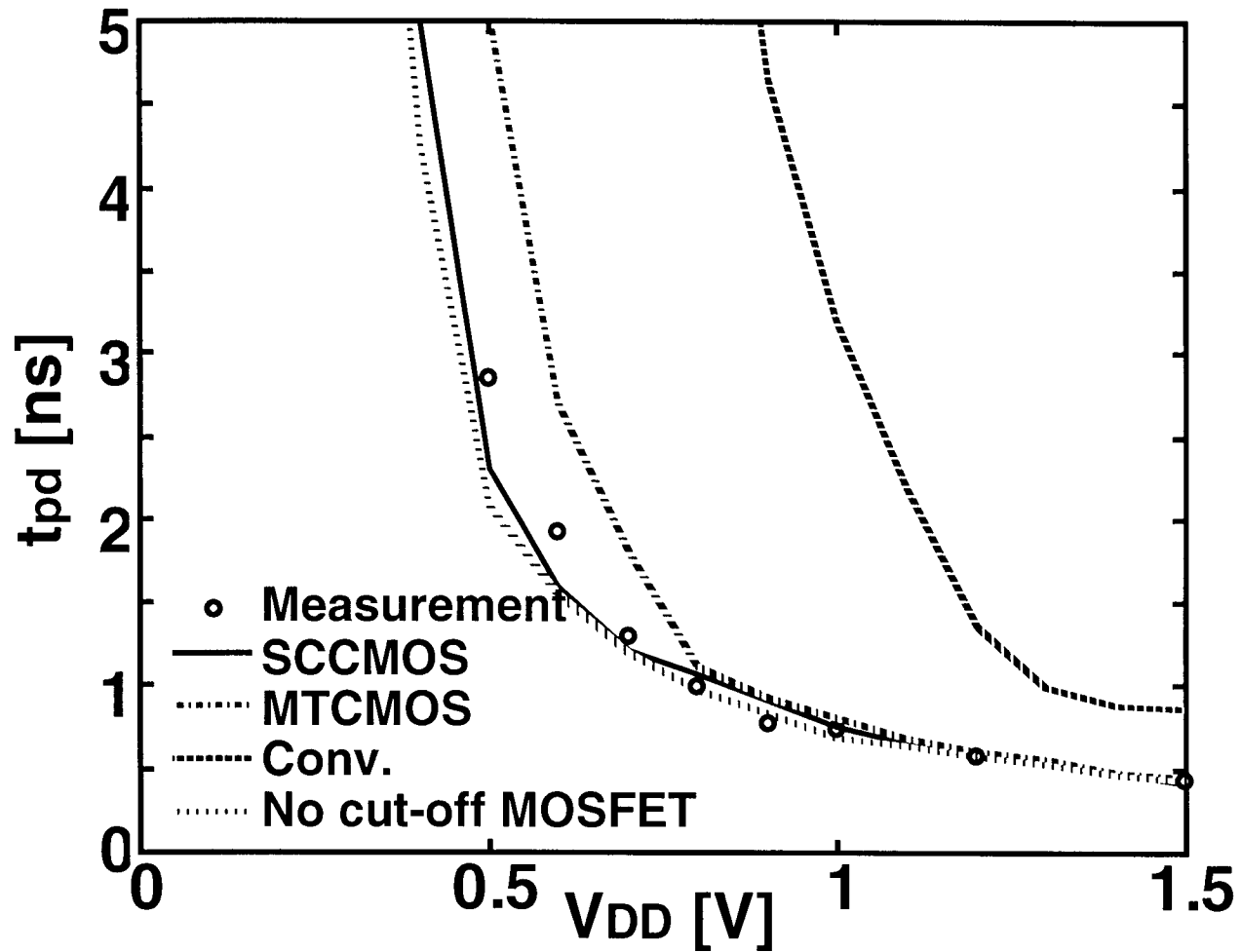
# Waveforms of special flip-flop



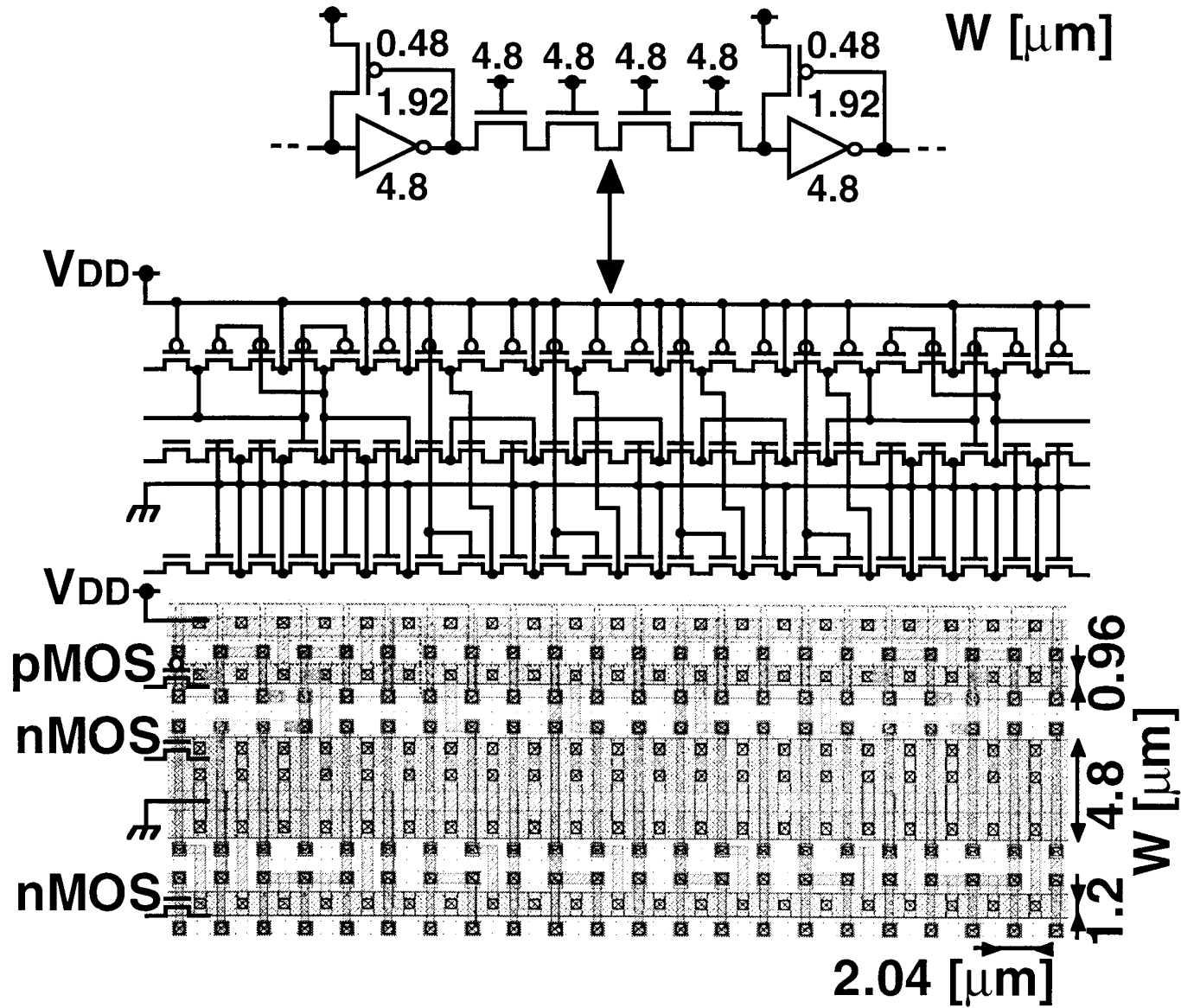
# Method to measure flip-flop delay



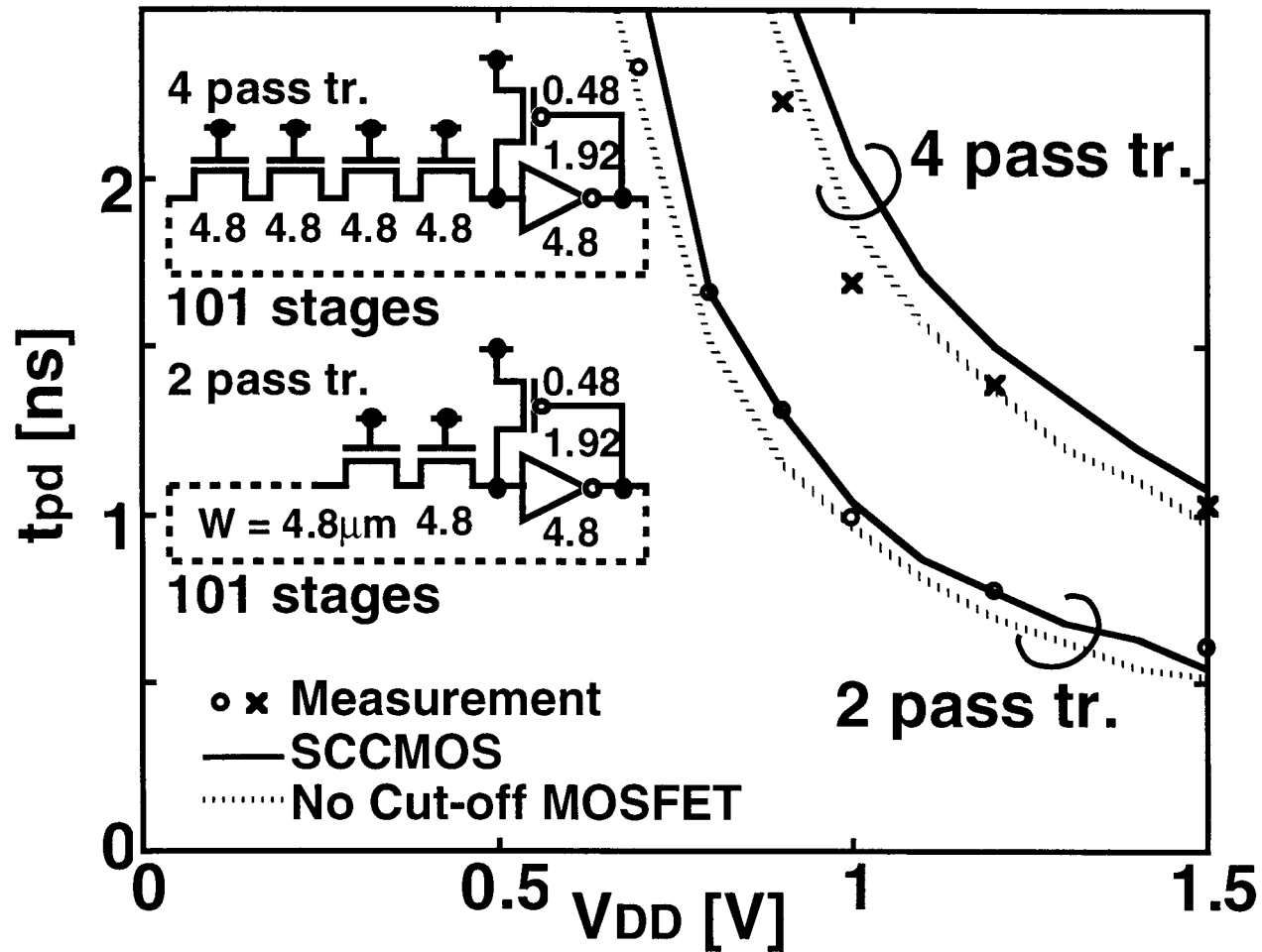
# Delay characteristics (flip-flop)



# Pass-transistor gate-array



# Delay characteristics (pass-tr. logic)





# Summary

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- **SCCMOS can operate down to 0.5V.**
- **SCCMOS can suppress leakage below 1pA per gate without speed degradation.**
- **Effective with SOI technology and/or pass-transistor logic.**